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"Exhibit B"

carrying out die-bonding under conditions of a temperature of from 150°C to 250 °C, a bonding time of 0.1 (inclusive) second to 2 seconds and a pressure of 0.1 gf/mm² to 4 gf/mm².

BRIEF DESCRIPTION OF THE DRAWINGS

5 Fig. 1 cross-sectionally illustrates an example of a process for fabricating the semiconductor device of the present invention.

Fig. 2 is a front elevation used to describe a method for measuring peel strength by using a push-pull gauge.

Fig. 3 is a plan view of an example of lead frames having a die pads.

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BEST MODE FOR CARRYING OUT THE INVENTION

The present invention will be described below in greater detail by giving Examples, but an embodiment of the present invention is not limited to these examples. All of polyimides used in the following examples are obtained by heating the mixture of acid dianhydride with diamine being the same mol as
15 the acid dianhydride, in solvent, so as to polymerize them. In the following examples, polyimide A is a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane; polyimide B is a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenylether; polyimide
20 C is a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane; polyimide D is a polyimide synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-